N-Channel 80-V (D-S) MOSFET

Key Features:

- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

Typical Applications:

- · White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

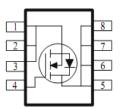
PRODUCT SUMMARY			
V _{DS} (V)	$r_{DS(on)}(m\Omega)$	I _D (A)	
80	11 @ V _{GS} = 10V	18	
80	13 @ $V_{GS} = 4.5V$	17	



FREE



DFN5X6-8L



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)							
Parameter	Symbol	Limit	Units				
Drain-Source Voltage	V_{DS}	80	V				
Gate-Source Voltage		V_{GS}	±20	V			
Continuous Drain Current a	T _A =25°C	I-	18				
Continuous Diairi Curient	T _A =70°C	I _D	15	Α			
Pulsed Drain Current ^b		I _{DM}	80				
Continuous Source Current (Diode Conduction) ^a		I _S	7.1	Α			
Dower Dissipation a	T _A =25°C	P _D	5	W			
Power Dissipation ^a	T _A =70°C	' D	3.2	VV			
Operating Junction and Storage Temperature Range		T_J,T_stg	-55 to 150	°C			

THERMAL RESISTANCE RATINGS							
Parameter	Symbol	Maximum	Units				
Maximum Junction-to-Ambient ^a	t <= 10 sec	$R_{\theta JA}$	25	°C/W			
Maximum Junction-to-Ambient	Steady State		65	C/VV			

1

Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Electrical Characteristics

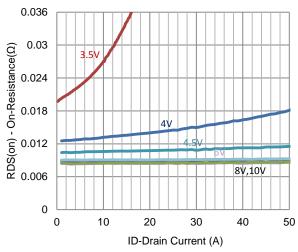
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit		
Static								
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250 \text{ uA}$	1			V		
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA		
Zero Gate Voltage Drain Current	lana	$V_{DS} = 64 \text{ V}, V_{GS} = 0 \text{ V}$			1	uА		
Zero Gate Voltage Brain Gurrent	I _{DSS}	$V_{DS} = 64 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			25			
On-State Drain Current	$I_{D(on)}$	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	40			Α		
Drain-Source On-Resistance	r	$V_{GS} = 10 \text{ V}, I_D = 14.4 \text{ A}$			11	mΩ		
Dialii-30dice Oil-Resistance	r _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 13.6 \text{ A}$			13	11152		
Forward Transconductance	g _{fs}	$V_{DS} = 15 \text{ V}, I_{D} = 14.4 \text{ A}$		25		S		
Diode Forward Voltage	V_{SD}	$I_S = 3.6 \text{ A}, V_{GS} = 0 \text{ V}$		0.7		V		
		Dynamic						
Total Gate Charge	Q_g	$V_{DS} = 40 \text{ V}, V_{GS} = 4.5 \text{ V},$		72				
Gate-Source Charge	Q_{gs}	$I_{DS} = 40 \text{ V}, V_{GS} = 4.3 \text{ V},$ $I_{D} = 14.4 \text{ A}$		15		nC		
Gate-Drain Charge	Q_gd	1D = 14.4 V		38				
Turn-On Delay Time	t _{d(on)}	$V_{DS} = 40 \text{ V}, R_{L} = 2.78 \Omega,$		20				
Rise Time	t _r	$V_{DS} = 40 \text{ V}, K_L - 2.76 \Omega,$ $I_D = 14.4 \text{ A},$		42		ne		
Turn-Off Delay Time	t _{d(off)}	$V_{GEN} = 10 \text{ V}, R_{GEN} = 6 \Omega$		172		ns		
Fall Time	t _f	VGEN = 10 V, NGEN = 0 12		63				
Input Capacitance	C _{iss}			4021				
Output Capacitance	C _{oss}	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		451		pF		
Reverse Transfer Capacitance	C_{rss}			440				

Notes

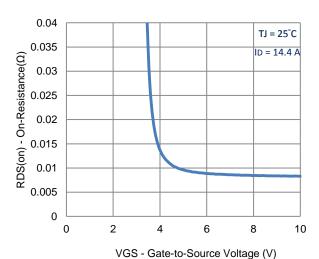
- Pulse test: PW <= 300us duty cycle <= 2%.
- Guaranteed by design, not subject to production testing. b.

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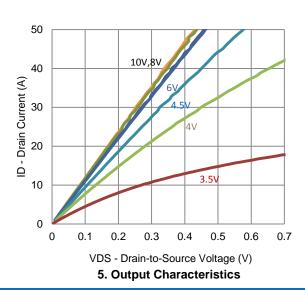
Typical Electrical Characteristics



1. On-Resistance vs. Drain Current



3. On-Resistance vs. Gate-to-Source Voltage



TJ = 25°C

40

40

40

40

20

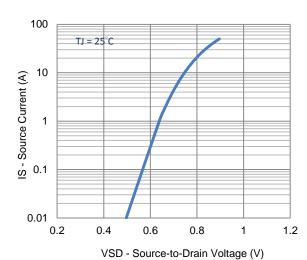
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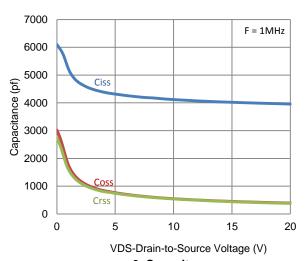
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VGS - Gate-to-Source Voltage (V)

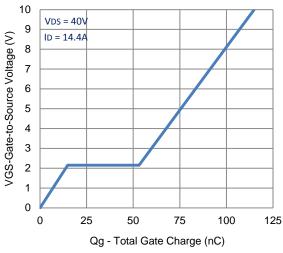
2. Transfer Characteristics

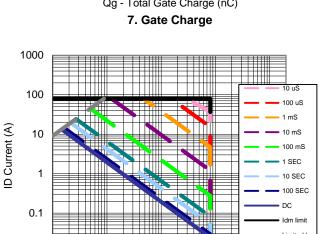


4. Drain-to-Source Forward Voltage



Typical Electrical Characteristics





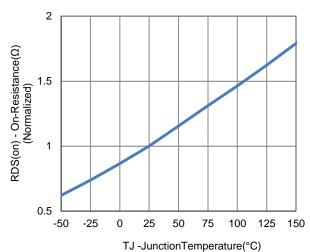
VDS Drain to Source Voltage (V)

9. Safe Operating Area

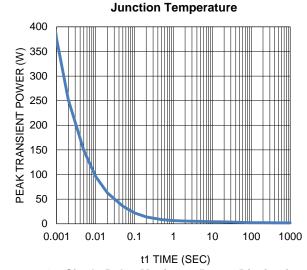
100

1000

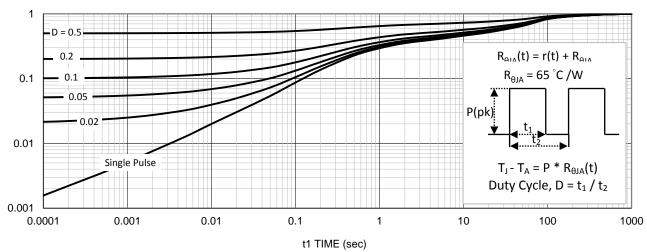
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8. Normalized On-Resistance Vs



10. Single Pulse Maximum Power Dissipation

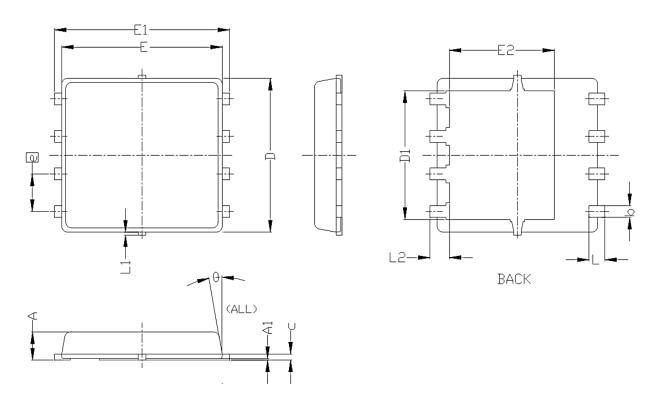


11. Normalized Thermal Transient Junction to Ambient

0.01

0.1

Package Information



SYMBOLS	DIMENSIONS IN MILLIMETERS		DIMENSIONS IN INCHES				
STMBULS	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.85	0.95	1.00	0.033	0.037	0.039	
Al	0.00		0.05	0.000		0.002	
b	0.30	0.40	0.50	0.012	0.016	0.020	
С	0.15	0. 20	0. 25	0.006	0.008	0.010	
D		5, 20 BSC			0. 205 BSC		
D1	4. 35 BSC			0. 171 BSC			
Е		5, 55 BSC 0, 219 BSC					
E1	6. 05 BSC		0. 238 BSC				
E2	3. 62 BSC			0. 143 BSC			
e	1. 27 BSC			0. 050 BSC			
L	0.45	0.55	0.65	0.018	0.022	0.026	
L1	0		0.15	0		0.006	
L2	0.68 REF			0.027 REF			
θ	0°		10°	0°		10°	